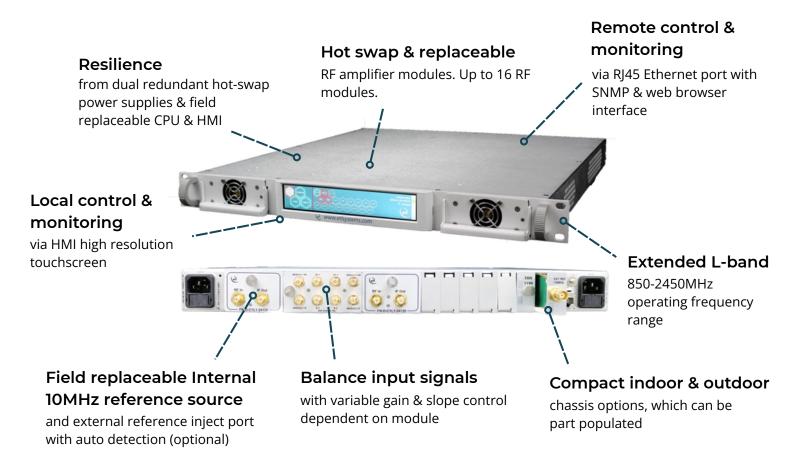


Alto L-band Redundant Amplifier Module

with low noise, high linearity, variable gain and slope control

ALT-G1R-S3-103 is an extended L-Band hot swap low noise & high linearity redundant amplifier with variable gain, designed to fit into the 1U Genus Redundant Chassis. The 1U redundancy chassis has the capacity for 1+1. 2+1 and 4+2 hot-swap module configurations.



Chassis Specification			
Dimensions/Weight/Colour	1U high x 550mm deep x 19" wide / <10kg / RAL9003 - white (semi-matte)		
Capacity	17 module slots. Note: Actual modules may require >1 slot. Refer to required module spec table.		
Temperature	Operating: 0°C to +45°C Storage: -20°C to +75°C		
Location/Humidity/Altitude	Indoor use only / 20 to 90% non-condensing / 2,000m AMSL (Operational) 8,000m AMSL (Storage) Above Mean Sea Level		
Control & Monitoring	Local: HMI, capacitive touch screen Remote: Ethernet via RJ45, 10BaseT/100 BaseTx. ETL TCP/IP, SNMPv2/3, HTTPS & built-in web server. HMI and CPU field replaceable.		
MTTR	20 minutes (15 minutes to retrieve spare part and 5 mins to replace). Applies to LRUs only and assumed in-house stock.		
AC Input/Consumption	85-264Vac 50/60Hz / 275W max. consumption at steady state		
PSU Redundancy	Dual redundant and alarmed. Diode OR. Hot swappable.		
Input & Output Ports	Dependent upon module fitted		

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Smart Amplifier Module

Compact form factor allows multiple modules to be housed in the 1U GENUS chassis. Each module occupies 1 slot in the chassis.

High linearity ensures overall RF gain signal performance is optimised.

Low noise for prime signal quality.

		1:1 Redundant Amplifier Module - RF F	Parameters
Model Numb	pers	ALT-G1R-S3-103 (The spec below is for ALT-G1R-S3-103 in 1:1 redundancy configuration with SWF-G1R-SX-101)	
Frequency Range		850 - 2450 MHz	
Size		1 slot wide	
RF Ports		50Ω SMA	
MTBF		>150,000 hrs. MTBF of each amp module. These are hot-swap	
Gain		42 ± 2.0 dB max. -7 ± 2.0 dB min.	
Gain	850 - 2450MHz	±1.0 dB	When set to 0dB slope. In manual gain control
Flatness	Any 36MHz	±0.3 dB	mode, not AGC.
Gain Steps		0.25 ± 0.15 dB in manual gain mode	
Slope Control Range		N/A	
Slope Control Steps		N/A	
Input Return Loss		16 dB typ. 12 dB min.	
Output Return Loss		16 dB typ. 12 dB min.	
Isolation		60dB Typ. 50dB Min.	With amplifiers set at the same gain level. Worst case isolation is between adjacent amps, isolation degrades dB to dB for different gain levels.
Reverse Gain		< -60 dB typ.	
	Тур.	5 dB	At max. gain
Noise Figure	Max.	6 dB	At max. gain
4 10 660	Тур.	19 dBm	At max. gain
1dB GCP	Min.	16 dBm	At max. gain
O.D.	Тур.	31 dBm	At max. gain
OIP3	Min.	28 dBm	At max. gain
0.100	Тур.	44 dBm	
OIP2	Min.	40 dBm	
In band, signal independent spurii		<-85 dBm max.	Very low level spurii from CPU clock, switch mode PSU and other control electronics inside the chassis.
Maximum Input Level		+20 dBm	For no damage. Non-operational.





Smart Amplifier Module

Compact form factor allows multiple modules to be housed in the 1U GENUS chassis. Each module occupies 1 slot in the chassis.

High linearity ensures overall RF gain signal performance is optimised.

Low noise for prime signal quality.

		2+1 Redundant Amplifier Module - RF F	Parameters
Model Numb	pers	ALT-G1R-S3-103 (The spec below is for ALT-G1R-S3-103 in 2+1 redundancy configuration with SWF-G1R-SX-114)	
Frequency Range		850 - 2450 MHz	
Size		1 slot wide	
RF Ports		50Ω SMA	
MTBF		>150,000 hrs. MTBF of each amp module. These are hot-swap	
Gain		38 ± 2.0 dB max. -11 ± 2.0 dB min.	
Gain	850 - 2450MHz	±1.2 dB	When set to 0dB slope. In manual gain control
Flatness	Any 36MHz	±0.3 dB	mode, not AGC.
Gain Steps		0.25 ± 0.15 dB in manual gain mode	
Slope Control Range		N/A	
Slope Control Steps		N/A	
Input Return Loss		14 dB typ. 10 dB min.	
Output Return Loss		14 dB typ. 10 dB min.	
Isolation		60dB Typ. 50dB Min.	With amplifiers set at the same gain level. Worst case isolation is between adjacent amps, isolation degrades dB to dB for different gain levels.
Reverse Gain		< -60 dB typ.	
	Тур.	6 dB	At max. gain
Noise Figure	Max.	7 dB	At max. gain
4 10 660	Тур.	19 dBm	At max. gain
1dB GCP	Min.	16 dBm	At max. gain
O.D.	Тур.	31 dBm	At max. gain
OIP3	Min.	28 dBm	At max. gain
OIP2	Тур.	41 dBm	
	Min.	37 dBm	
In band, signal independent spurii		<-85 dBm max.	Very low level spurii from CPU clock, switch mode PSU and other control electronics inside the chassis.
Maximum Input Level		+20 dBm	For no damage. Non-operational.





Smart Amplifier Module

Compact form factor allows multiple modules to be housed in the 1U GENUS chassis. Each module occupies 1 slot in the chassis.

High linearity ensures overall RF gain signal performance is optimised.

Low noise for prime signal quality.

		4+2 Redundant Amplifier Module - RF I	Parameters
Model Numb	ers	ALT-G1R-S3-103 (The spec below is for ALT-G1R-S3-103 in 4+2 redundancy configuration with SWF-G1R-S5-103-S5S5)	
Frequency Range		850 - 2450 MHz	
Size		1 slot wide	
RF Ports		50Ω SMA	
MTBF		>150,000 hrs. MTBF of each amp module. These are hot-swap	
Gain		36 ± 2.0 dB max. -13 ± 2.0 dB min.	
Gain	850 - 2450MHz	±1.2 dB	When set to 0dB slope. In manual gain control
Flatness	Any 36MHz	±0.3 dB	mode, not AGC.
Gain Steps		0.25 ± 0.15 dB in manual gain mode	
Slope Control Range			N/A
Slope Control Steps		N/A	
Input Return Loss		14 dB typ. 10 dB min.	
Output Return Loss		14 dB typ.	10 dB min.
Isolation		60 dB Typ. (850-2150MHz) 50 dB Min. (850-2150MHz) 55 dB Typ. (2150-2450MHz) 45 dB Min. (2150-2450MHz)	With amplifiers set at the same gain level. Worst case isolation is between adjacent amps, isolation degrades dB to dB for different gain levels.
Reverse Gain		< -60 dB typ.	
	Тур.	6 dB	At max. gain
Noise Figure	Max.	8 dB	At max. gain
4 10 660	Тур.	18 dBm	At max. gain
1dB GCP	Min.	15 dBm	At max. gain
O.D.O.	Тур.	30 dBm	At max. gain
OIP3	Min.	27 dBm	At max. gain
OID3	Тур.	40 dBm	
OIP2	Min.	36 dBm	
In band, signal independent spurii		<-85 dBm max.	Very low level spurii from CPU clock, switch mode PSU and other control electronics inside the chassis.
Maximum Input Level		+20 dBm	For no damage. Non-operational.



Interface, Monitoring & Alarms				
Control Method	Local and remote as provided by selected chassis			
LNB Power	None			
On a ratio a Tanana ratura	-0°C to +50°C	Up to 8 modules in a chassis.		
Operating Temperature	-0°C to +45°C	Up to 16 modules in a chassis.		
Storage Temperature	-20°C to +75°C			
Location	Indoor use only, within parent GENUS chassis			
Humidity	20 to 90% non-condensing, relative humidity			
Altitude	10,000ft / 3,000m above mean sea level			
Physical Dimensions & Parameters				
Weight	<0.35kg typ.			

The performance quoted above is for a standalone amplifier. For in-chassis performance, see relevant spec. tables.

Note 1: The specification is subject to regular reviews and will be updated from time to time as part of our continuing product development and improved spec accuracy.

Note 2: Operation beyond the quoted limits stated above may cause instantaneous and permanent damage.